## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE :

In resistant and cation of

Bojarczuk, Jr., et al.

Serial No.: 10/059,422

Group Art Unit: 2814

Filing Date: January 31, 2002

Examiner: Doan, Theresa T.

For: METHOD OF FORMING LATTICE-MATCHED STRUCTURE ON SILICON AND

STRUCTURE FORMED THEREBY

Honorable Commissioner of Patents Alexandria, Virginia 22313-1450

## INFORMATION DISCLOSURE STATEMENT

Sir:

Under the provisions of 37 CFR §1.97 through §1.99 and pursuant to applicant's duty of disclosure under 37 CFR §1.56, applicant respectfully brings the following document listed on the attached form PTO-1449, to the attention of the Examiner in charge of the above-identified application. This reference was either cited or submitted in parent Application No. 69/898,039.

This citation does not constitute an admission that the reference is relevant or material to the claims. It is only cited as constituting related art of which the applicant is aware.

It is respectfully requested that the listed reference be considered by the Examiner and formally made of record in this application.

Submitted herewith is a check in the amount of \$180.00 to cover the IDS fee.

Please charge any deficiencies in fees and credit any overpayment of fees to Assignee's Deposit Account No. 50-0510.

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Respectfully submitted,

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